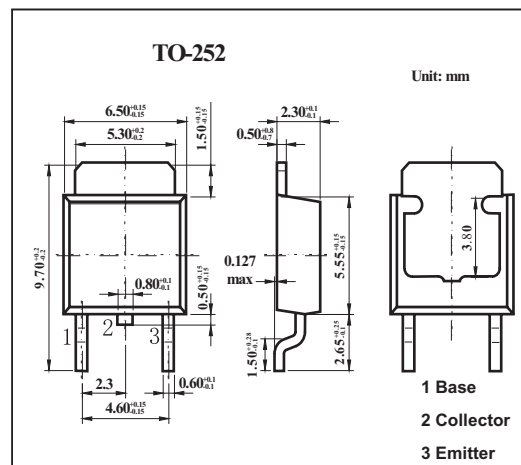


Silicon NPN Epitaxial

2SD2121S

■ Features

- Low frequency power amplifier.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	35	V
Collector to emitter voltage	V_{CEO}	35	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	2.5	A
Peak collector current	I_{CP}	3	A
Collector power dissipation $T_c = 25^\circ\text{C}$	P_C	18	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1\text{ mA}, I_E = 0$	35			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, R_{BE} = \infty$	35			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1\text{ mA}, I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB} = 35\text{ V}, I_E = 0$			20	μA
DC current transfer ratio *	h_{FE}	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	60		320	
		$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$	20			
Base to emitter voltage *	V_{BE}	$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$			1.5	V
Collector to emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 2\text{ A}, I_B = 0.2\text{ A}$			1.0	V

* Pulse test.

■ h_{FE} Classification

Marking	B	C	D
h_{FE}	60~120	100~200	160~320